

deep recesses, and other features found in connection with intricate geometries. For devices having more coarse features, electroplating or sputtering may be suitable.

Please replace the paragraph at page 6, lines 17-23 with the following paragraph (marked up version attached in Appendix):

Figure 3A shows a wafer 40 and an area 42 of the wafer 40 to which it is desired that the armored coating be applied. The first step of applying a partial armored coating to the wafer 40 is shown in Figure 3B. Figure 3B illustrates applying photo resist 44 to the wafer 40 on all areas of the wafer 40 but the area 42 which is to be armor coated. Next, as shown in Figure 3C, a seed layer 46 is deposited on the wafer 40. The seed layer 46 covers both the photo resist 44 as well as the area 42 to be armor coated.

IN THE CLAIMS

Please add new claims 21-25, such that pending claims 1-25 are as follows:

1. A microelectromechanical component formed of silicon, the component comprising a feature on the component which is subjected to a mechanical stress, and means for increasing robustness of the feature
2. The component of claim 1 wherein means for increasing robustness of the feature comprises coating the feature with a ductile material
3. The component of claim 2 wherein the ductile material comprises a metal
4. The component of claim 1 wherein means for increasing the robustness of the feature comprises coating the component with a ductile material
5. The component of claim 4 wherein the ductile material comprises a metal
6. A microcomponent formed of silicon, the microcomponent comprising

a feature on the microcomponent which is subjected to a mechanical stress, and
a ductile material coating the feature to increase robustness of the
microcomponent

7. The microcomponent of claim 6 wherein the ductile material comprises a metal

8. The microcomponent of claim 7 and further comprising a seed layer to facilitate the
ability of the metal to coat the feature.

9. The microcomponent of claim 7 wherein the metal has a thickness of about 10
microns.

10. The micro component of claim 6 wherein the ductile material coating the feature
prevents the silicon from chipping or breaking near the feature which is subjected to a mechanical
stress.

11. The micro component of claim 6 and further comprising a ductile material coating
substantially the entire surface of the micro component.

12. A method of increasing the robustness of an area on a microelectromechanical
components, the method comprising:

forming the microelectromechanical component from silicon; and
coating a selected area on the component which is subjected to a mechanical stress
with a ductile material.

13. The method of claim 12 wherein forming the component from silicon comprises
forming a plurality of components from a silicon wafer

14. The method of claim 13 wherein coating the component with a ductile material comprises coating a preselected area of the component with a metal

15. The method of claim 14 wherein coating a preselected area of the component with a metal comprises.

applying photo resist to the component to define an area to which the metal will be applied,

depositing a seed layer on the component,

removing the photo resist so that the seed layer remains only in the area to which the metal will be applied; and

applying a metal coating to the seed layer.

16. The method of claim 15 wherein applying the metal coating to the seed layer comprises using a chemical vapor deposition process.

17. The method of claim 15 wherein applying the metal coating to the seed layer comprises using an electroplating process.

18. The method of claim 15 wherein applying the metal coating to the seed layer comprises using a sputtering process

19. The method of claim 15 wherein applying the metal coating comprises applying the metal coating to a thickness of up to about 10 microns

20. The method of claim 15 wherein applying the metal coating comprises applying the metal coating to a thickness of up to about 20 microns